L Number	Hits	Search Text	DB	Time stamp
15	1148199	(((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous and active region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:42
16	0	(((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous and active adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:38
17	0	(((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous and transistor with active adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:39
18	0	(((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:40
19	20	nonporous and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:40
20	9	(((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:43
21	1	((((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous) and (tft or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:44
22	1		USPAT; US-PGPUB	2002/06/11 15:48
23	1		USPAT; US-PGPUB	2002/06/11 16:01
–	673	((438/311) or (438/149) or (438/150) or (438/378)).CCLS.	USPAT; US-PGPUB	2002/06/10 17:05
–	339	(((438/311) or (438/149) or (438/150) or (438/378)).CCLS.) and anneal$3	USPAT; US-PGPUB	2002/06/10 17:05
–	106	((((438/311) or (438/149) or (438/150) or (438/378)).CCLS.) and anneal$3) and (soi or (silicon adj on adj insulator))	USPAT; US-PGPUB	2002/06/10 17:06
–	12	(((((438/311) or (438/149) or (438/150) or (438/378)).CCLS.) and anneal$3) and (soi or (silicon adj on adj insulator))) and (single-crystal adj silicon)	USPAT; US-PGPUB	2002/06/10 20:12
–	469	(soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)	USPAT; US-PGPUB	2002/06/10 20:13
–	595	(soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/10 20:13
–	289	((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/10 20:13
–	285	(((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/10 20:14

-	28	(((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/10 20:15
-	9	(((((soi or (silicon adj on adj insulator)) and (single-crystal adj silicon)) and anneal$3) and substrate) and reduc$3 adj atmosphere) and nonporous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/11 15:36